

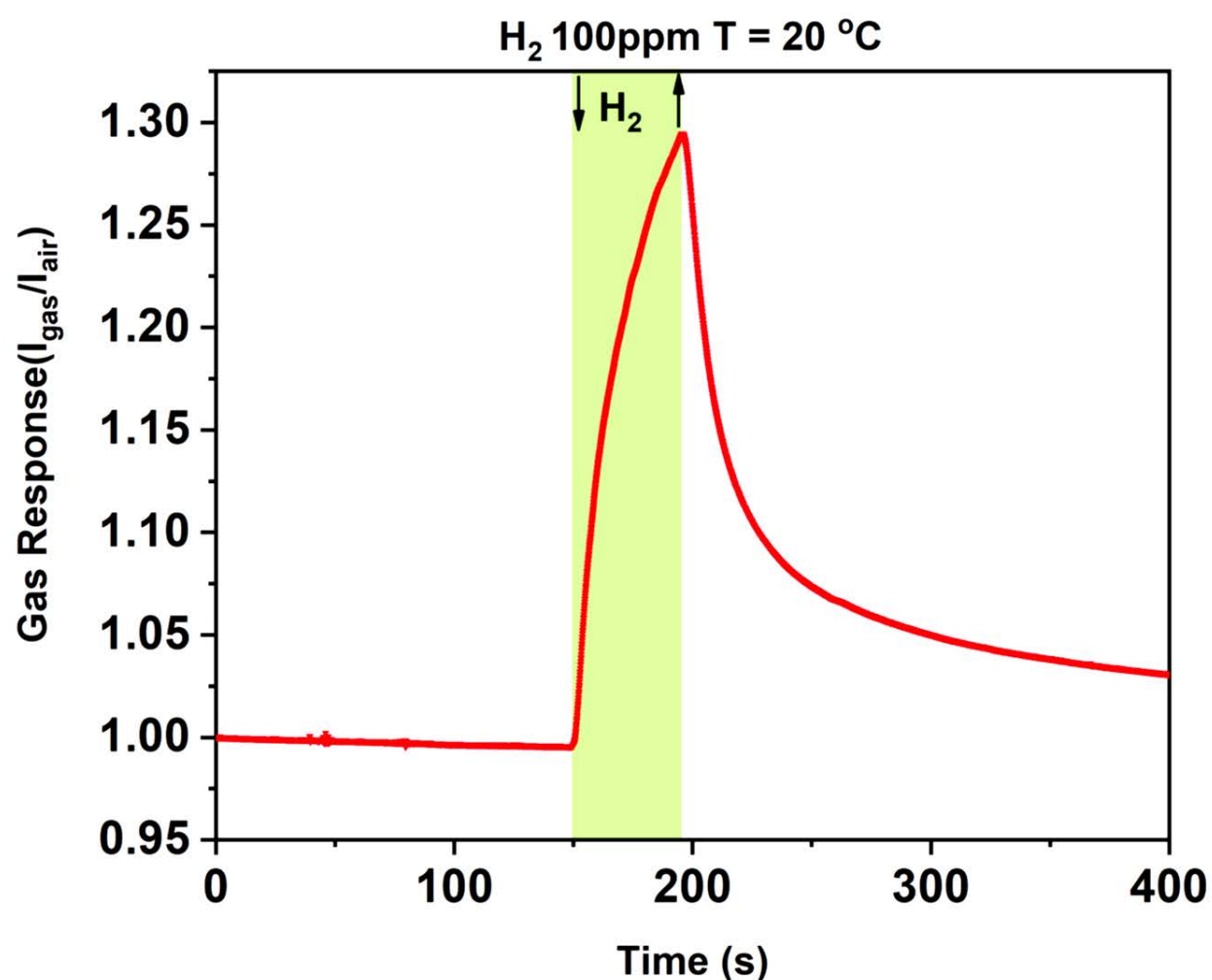
ZnO:Eu FILMS FUNCTIONALIZED WITH Pd FOR ROOM TEMPERATURE H₂ SENSORS

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The invention relates to the technology for deposition of semiconductor oxide films, in particular to the process of obtaining of ZnO:Eu³⁺ films, with application of rapid thermal annealing ($T=650\text{ }^{\circ}\text{C}$, $t=60\text{ s}$), with can be applied to the manufacture of gas sensors obtaining sensibility $S=I_{\text{gas}}/I_{\text{air}}=1.3$ for 100 ppm H₂ gas at room temperature and $S=I_{\text{gas}}/I_{\text{air}}=118$ at operating temperature of 250 oC.



Concept of ZnO:Eu FILMS
FUNCTIONALIZED WITH Pd FOR ROOM TEMPERATURE H₂ SENSORS.

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